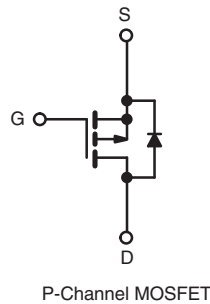
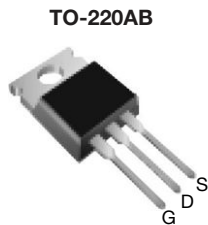


Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 60
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V 0.14
Q_g (Max.) (nC)	34
Q_{gs} (nC)	9.9
Q_{gd} (nC)	16
Configuration	Single



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- P-Channel
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



Available
RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRF9Z34PbF SiHF9Z34-E3
SnPb	IRF9Z34 SiHF9Z34

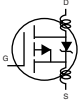

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	- 60	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	V_{GS} at - 10 V	$T_C = 25^\circ\text{C}$	- 18	A
		$T_C = 100^\circ\text{C}$	- 13	
Pulsed Drain Current ^a	I_{DM}	- 72		
Linear Derating Factor		0.59	W/°C	
Single Pulse Avalanche Energy ^b	E_{AS}	370	mJ	
Repetitive Avalanche Current ^a	I_{AR}	- 18	A	
Repetitive Avalanche Energy ^a	E_{AR}	8.8	mJ	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	88	W
Peak Diode Recovery dV/dt^c		dV/dt	- 4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d		
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = -25$ V, starting $T_J = 25^\circ\text{C}$, $L = 1.3$ mH, $R_g = 25 \Omega$, $I_{AS} = -18$ A (see fig. 12).
- $I_{SD} \leq -18$ A, $dI/dt \leq 170$ A/ μs , $V_{DD} \leq V_{DS}$, $T_J \leq 175^\circ\text{C}$.
- 1.6 mm from case.

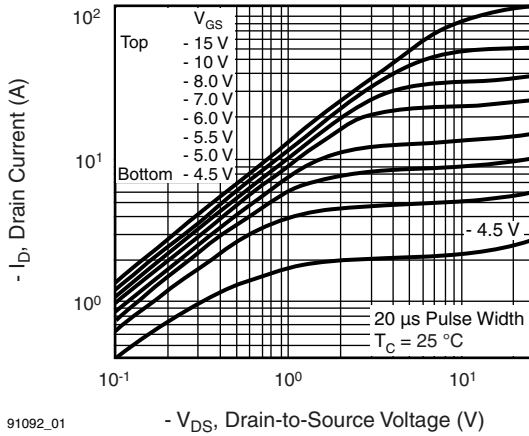
* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

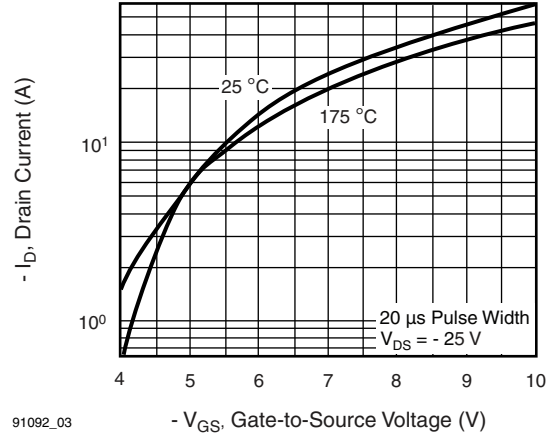
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$	-	-0.060	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$	-	-	-100	μA
		$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -11\text{ A}^b$	-	-	0.14	Ω
Forward Transconductance	g_{fs}	$V_{DS} = -25\text{ V}, I_D = -11\text{ A}^b$	5.9	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5	-	1100	-	pF
Output Capacitance	C_{oss}		-	620	-	
Reverse Transfer Capacitance	C_{rss}		-	100	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}, I_D = -1.8\text{ A}, V_{DS} = -48\text{ V}$, see fig. 6 and 13 ^b	-	-	34	nC
Gate-Source Charge	Q_{gs}		-	-	9.9	
Gate-Drain Charge	Q_{gd}		-	-	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}, I_D = -18\text{ A}, R_g = 12\text{ }\Omega, R_D = 1.5\text{ }\Omega$, see fig. 10 ^b	-	18	-	ns
Rise Time	t_r		-	120	-	
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	
Fall Time	t_f		-	58	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	-18	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	-72	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -18\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	-6.3	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -18\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	100	200	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.28	0.52	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

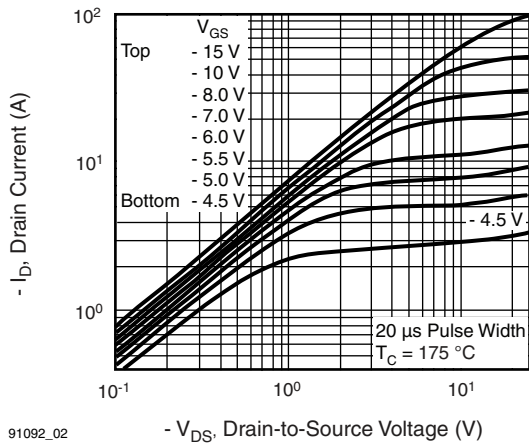
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


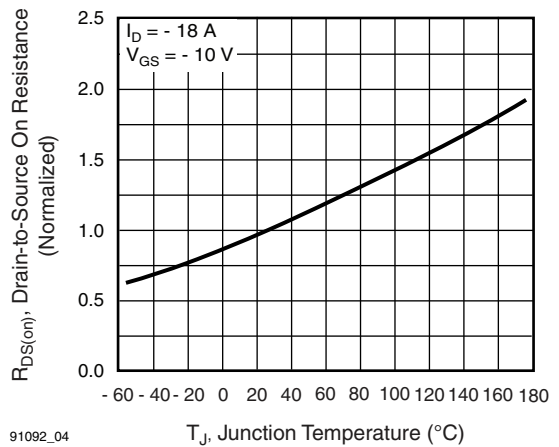
91092_01

Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$


91092_03

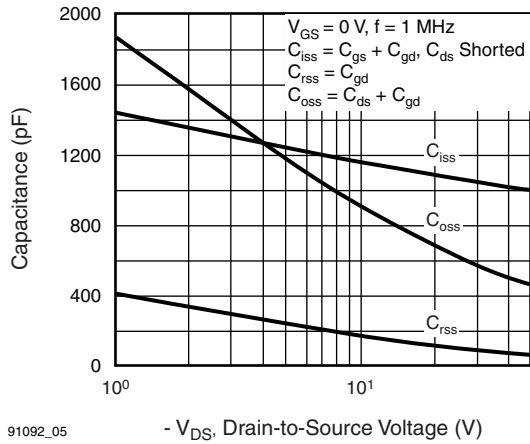
Fig. 3 - Typical Transfer Characteristics


91092_02

Fig. 2 - Typical Output Characteristics, $T_C = 175^\circ\text{C}$


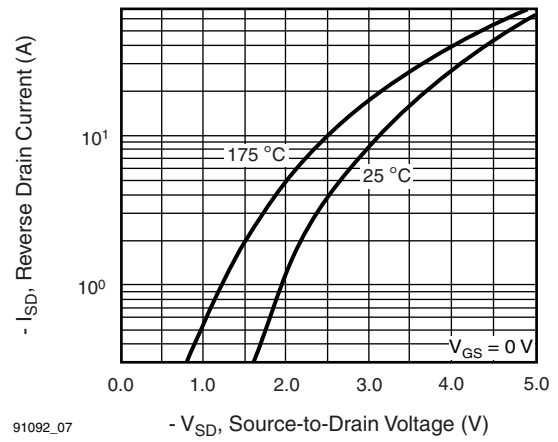
91092_04

Fig. 4 - Normalized On-Resistance vs. Temperature



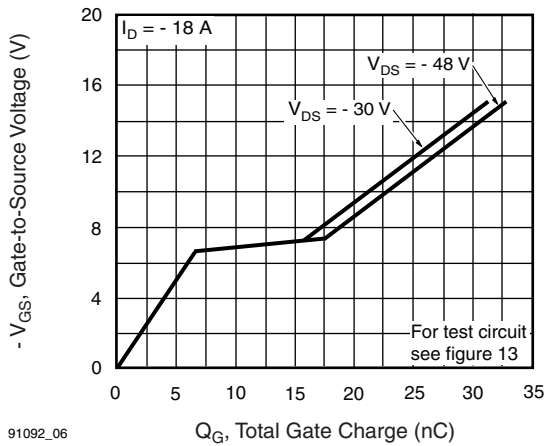
91092_05

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



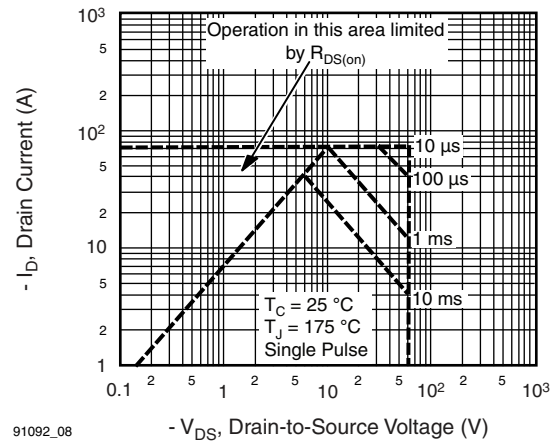
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91092_06

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91092_08

Fig. 8 - Maximum Safe Operating Area

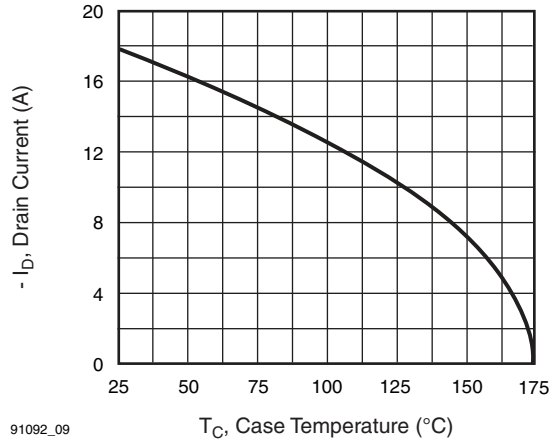


Fig. 9 - Maximum Drain Current vs. Case Temperature

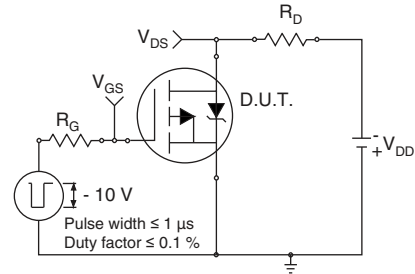


Fig. 10a - Switching Time Test Circuit

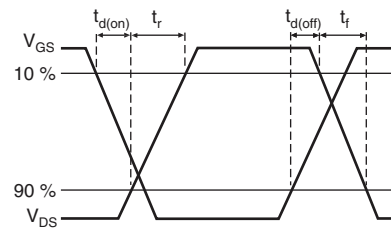


Fig. 10b - Switching Time Waveforms

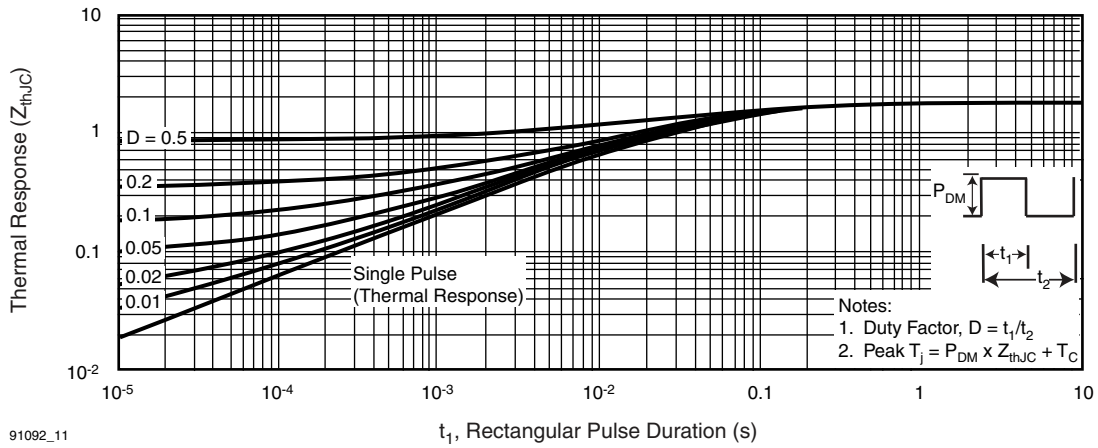


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

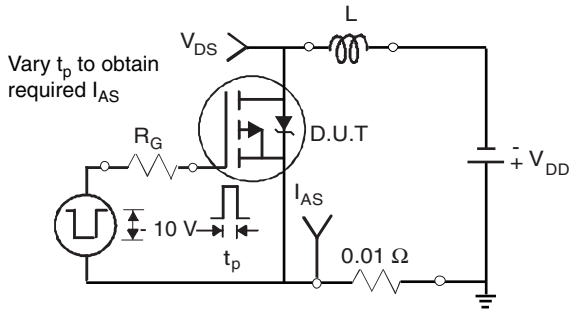


Fig. 12a - Unclamped Inductive Test Circuit

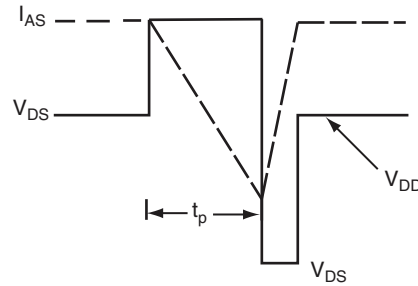
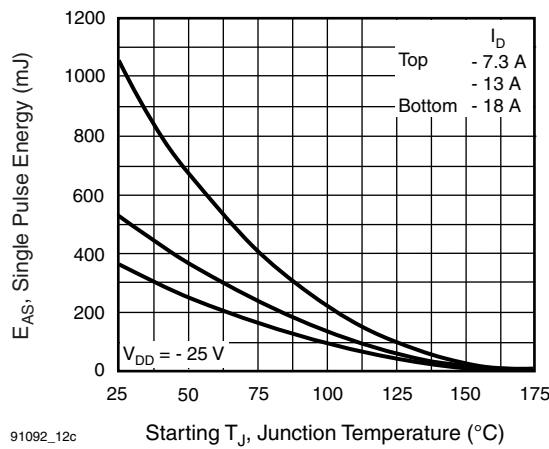


Fig. 12b - Unclamped Inductive Waveforms



91092_12c

Fig. 12c - Maximum Avalanche Energy vs. Drain Current

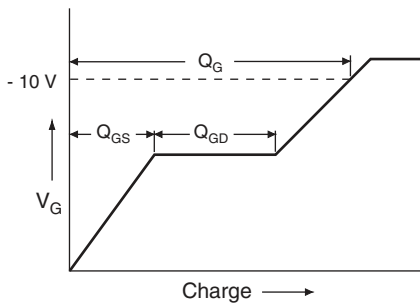


Fig. 13a - Basic Gate Charge Waveform

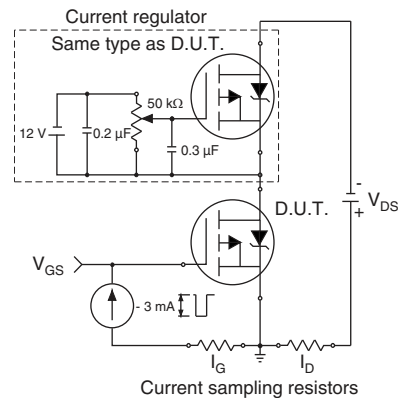
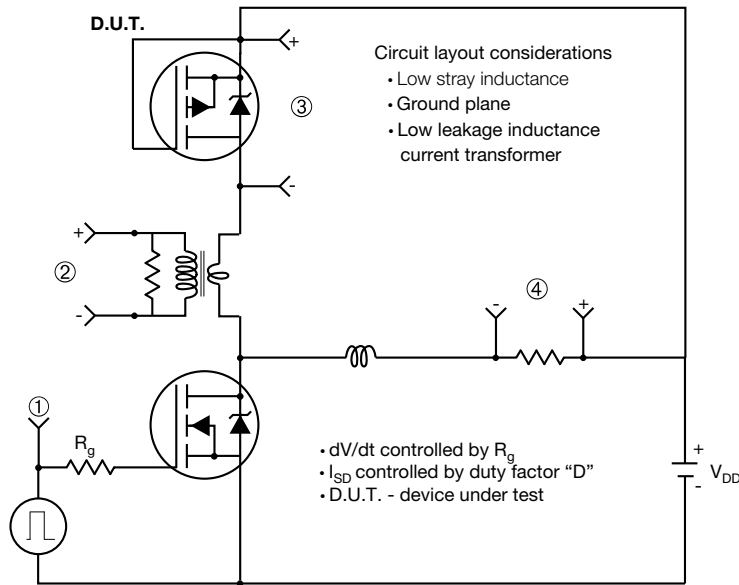


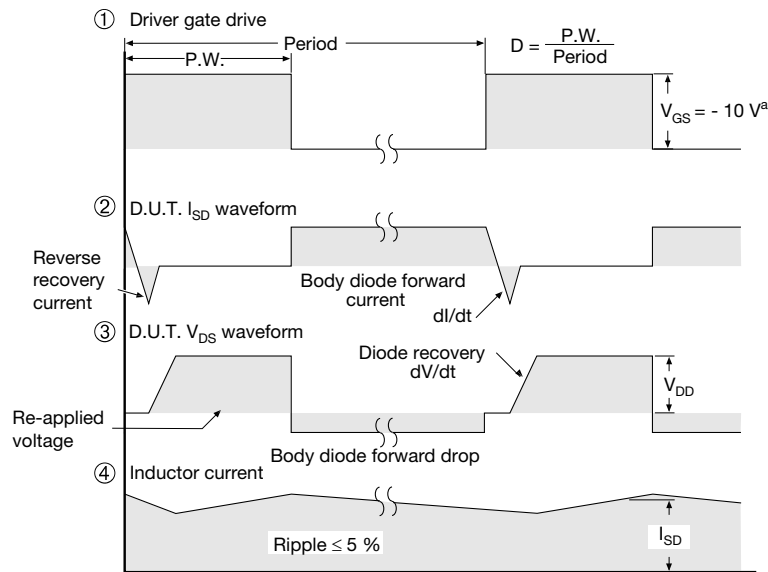
Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

- Compliment N-Channel of D.U.T. for driver



Note

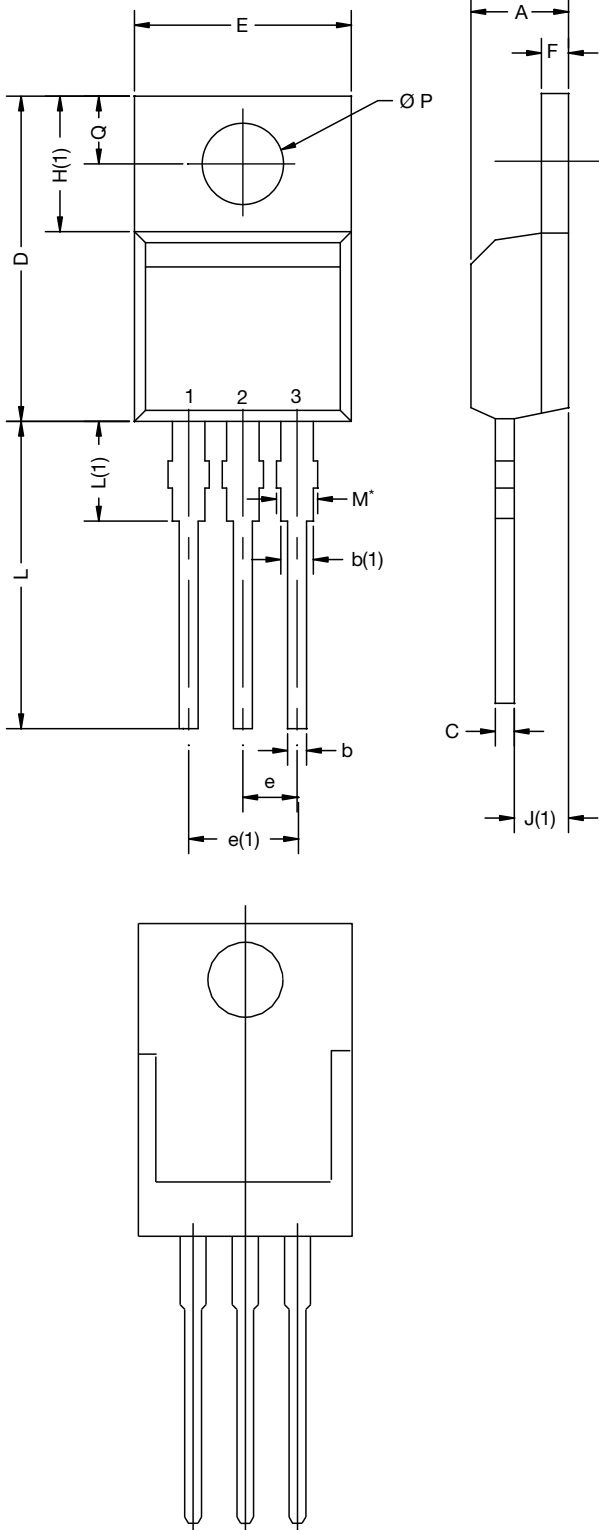
a. $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 14 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?91092>.



TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.14	4.70	0.163	0.185
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.32	15.86	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	0.51	1.40	0.020	0.055
H(1)	6.10	6.70	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.05	0.131	0.159
$\varnothing P$	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0339-Rev. B, 02-Nov-15
DWG: 6031

Note

- M^* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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